Title (en)

VERTICAL FIELD-EFFECT TRANSISTOR AND METHOD FOR FORMING SAME

Title (de)

VERTIKALER FELDEFFEKTTRANSISTOR UND VERFAHREN ZUM AUSBILDEN DESSELBEN

Title (fr)

TRANSISTOR À EFFET DE CHAMP VERTICAL ET SON PROCÉDÉ DE FORMATION

Publication

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Application

EP 20776124 A 20200921

Priority

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Abstract (en)

[origin: WO2021078451A1] The invention relates to a vertical field effect transistor (200) comprising: a drift region (212) having a first conductivity type, a semiconductor fin (302) that is on or above the drift region (212), a source/drain electrode (202) that is on or above the semiconductor fin (212) and a shielding structure (214) that is arranged laterally adjacent to the at least one lateral wall of the semi-conductor fin (302) in the drift region (212). The shielding structure (214) has a second conductivity type which is different from the first conductivity type and the semi-conductor fin (302) is connected in an electrically conductive manner to the source/drain electrode (202).

IPC 8 full level

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CPC (source: CN EP US)

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